

N-Channel Power MOSFET

30V, 90A, 5.2mΩ

FEATURES

- Low R_{DS(ON)} to minimize conductive losses
- Low gate charge for fast power switching
- 100% UIS and R_g tested
- 175°C Operating Junction Temperature
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS				
PARAMETER		VALUE	UNIT	
V_{DS}		30	V	
R _{DS(on)}	$V_{GS} = 10V$	5.2	mΩ	
(max)	$V_{GS} = 4.5V$	8		
Q_g		21	nC	



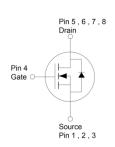




APPLICATIONS

- DC-DC Converter
- Battery Management
- Load Switch
- Motor Drive





Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$	l _D	90		
	$T_A = 25$ °C		17	_ A	
Pulsed Drain Current		I _{DM}	360	А	
Single Pulse Avalanche Current (Note 2)		I _{AS}	28	А	
Single Pulse Avalanche Energy (Note 2)		E _{AS}	118	mJ	
Total Power Dissipation	$T_C = 25^{\circ}C$	P _D	83	10/	
	$T_C = 125$ °C		28	W	
Total Power Dissipation	$T_A = 25$ °C	Б	3.1	\\\	
	$T_A = 125^{\circ}C$	P _D	1	W	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +175	°C	

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	MAXIMUM	UNIT		
Junction to Case Thermal Resistance	R _{eJC}	1.8	°C/W		
Junction to Ambient Thermal Resistance	R _{e.IA}	48	°C/W		

Thermal Performance Note: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JC}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. The $R_{\Theta JA}$ limit presented here is based on mounting on a 1 in² pad of 2 oz copper.

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PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	30			V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1	1.6	2.5	V
Gate-Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
	$V_{GS} = 0V, V_{DS} = 30V$				1	
Drain-Source Leakage Current	$V_{GS} = 0V, V_{DS} = 30V$ $T_{J} = 125^{\circ}C$	I _{DSS}		100	μΑ	
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 17A$			3.2	5.2	mΩ
(Note 3)	$V_{GS} = 4.5V, I_D = 14A$	R _{DS(on)}	-	5	8	
Forward Transconductance (Note 3)	$V_{DS} = 10V, I_{D} = 17A$	9 _{fs}		50		S
Dynamic (Note 4)						
Total Gate Charge	$V_{GS} = 10V, V_{DS} = 15V,$ $I_{D} = 17A$	Q_g		41		
Total Gate Charge	$V_{GS} = 4.5V, V_{DS} = 15V,$ $I_{D} = 14A$	Qg		21		nC
Gate-Source Charge		Q _{gs}		5		
Gate-Drain Charge		Q_{gd}		13		
Input Capacitance		C _{iss}		2294		
Output Capacitance	$V_{GS} = 0V, V_{DS} = 15V,$	C _{oss}		386		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		249		
Gate Resistance	f = 1.0MHz	R_g	0.4	1.3	2.6	Ω
Switching (Note 4)						
Turn-On Delay Time		t _{d(on)}		6		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 15V,$ $I_D = 17A, R_G = 2\Omega$	t _r		15		
Turn-Off Delay Time		t _{d(off)}		22		ns
Turn-Off Fall Time		t _f		9		
Source-Drain Diode						
Forward Voltage (Note 3)	$V_{GS} = 0V, I_{S} = 17A$	V _{SD}			1	V
Reverse Recovery Time	I _S = 17A,	t _{rr}	-	23		ns
Reverse Recovery Charge	dl/dt = 100A/µs	Q _{rr}		16		nC

Notes:

- 1. Silicon limited current only.
- 2. L = 0.3mH, $V_{GS} = 10$ V, $V_{DD} = 25$ V, $R_G = 25\Omega$, $I_{AS} = 28$ A, Starting $T_J = 25$ °C
- 3. Pulse test: Pulse Width \leq 300 μ s, duty cycle \leq 2%.
- 4. Switching time is essentially independent of operating temperature.

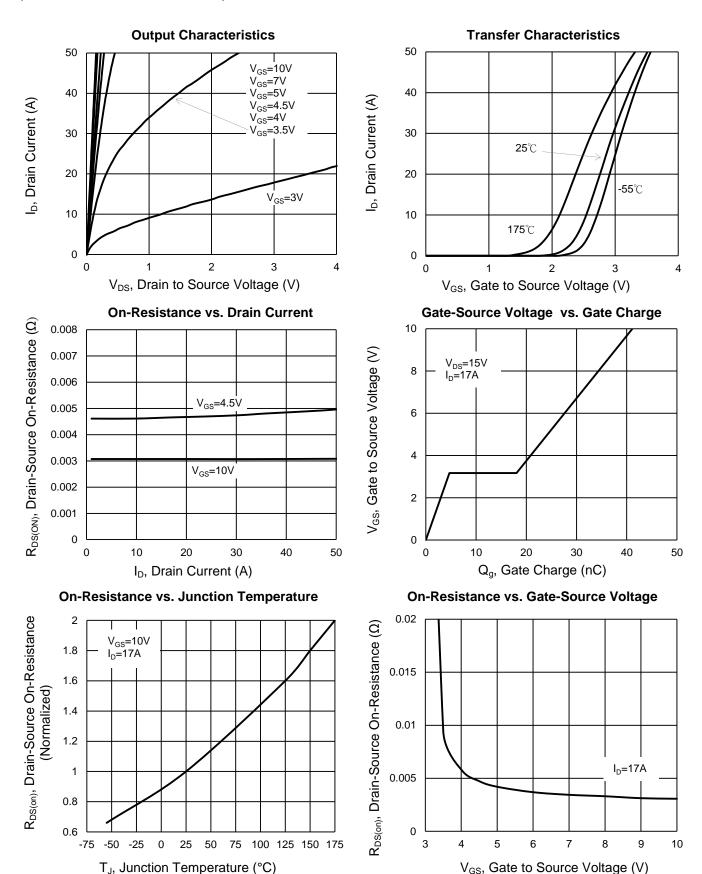
ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM052NB03CR RLG	PDFN56	2,500pcs / 13" Reel



CHARACTERISTICS CURVES

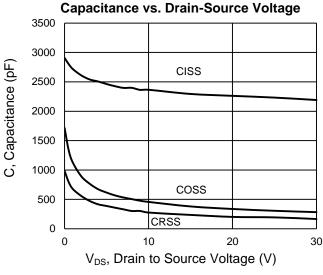
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

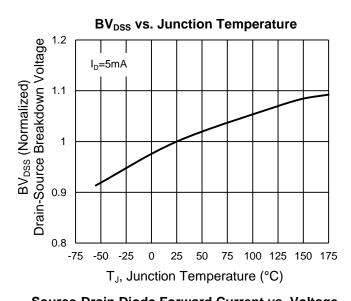


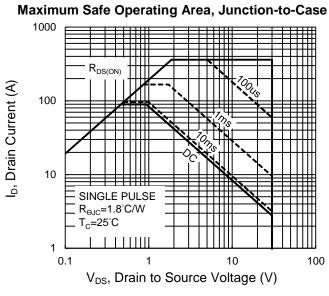


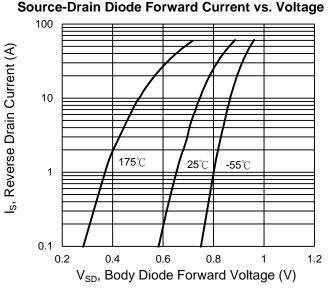
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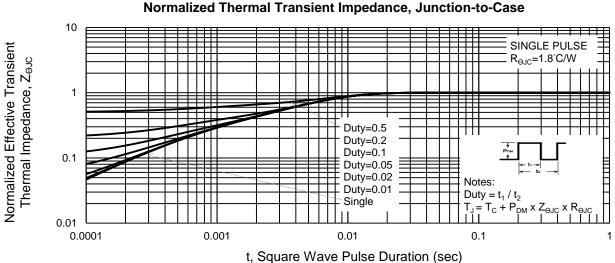
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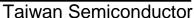






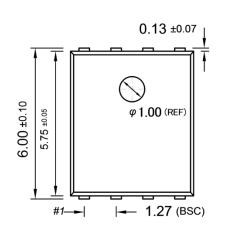


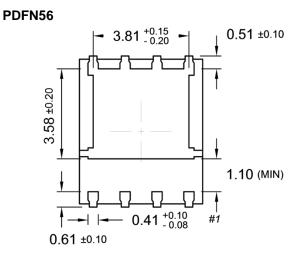
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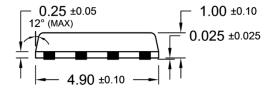




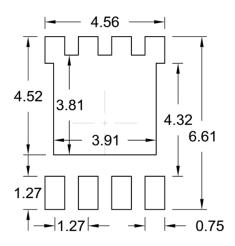
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)







SUGGESTED PAD LAYOUT (Unit: Millimeters)



5

MARKING DIAGRAM



Y = Year Code

WW = Week Code (01~52)

L = Lot Code (1~9,A~Z)

F = Factory Code



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